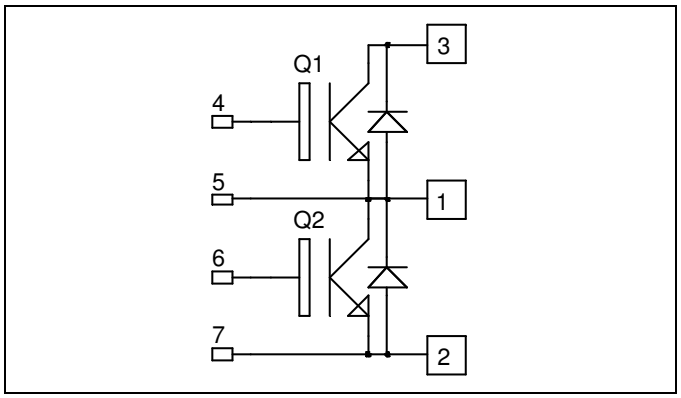
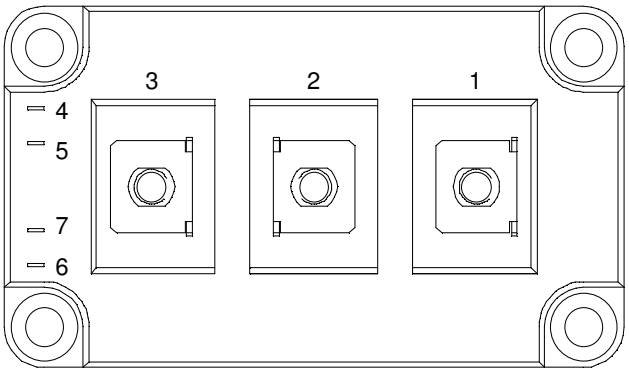
Phase Leg
Trench IGBT® Power Module

V_{CES} = 1200V
I_C = 200A @ Tc = 80°C





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT® Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
  - M6 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_C = 25°C	300	A
		T_C = 80°C	200	
I_{CM}	Pulsed Collector Current	T_C = 25°C	400	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	1040	W
SCSOA	Short Circuit Safe Operating Area	T_j = 125°C	800A@900V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
BV_{CES}	Collector - Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 6mA		1200			V
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1200V				6	mA
$V_{CE(on)}$	Collector Emitter on Voltage	V_{GE} = 15V, I_C = 200A	T_j = 25°C	1.4	1.7	2.1	V
			T_j = 125°C		2.0		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 6mA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				600	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz		14		nF
C_{oes}	Output Capacitance			0.8		
C_{res}	Reverse Transfer Capacitance			0.66		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 200A R_G = 3.6Ω		280		ns
T_r	Rise Time			90		
$T_{d(off)}$	Turn-off Delay Time			550		
T_f	Fall Time			130		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 200A R_G = 3.6Ω		300		ns
T_r	Rise Time			100		
$T_{d(off)}$	Turn-off Delay Time			650		
T_f	Fall Time			180		

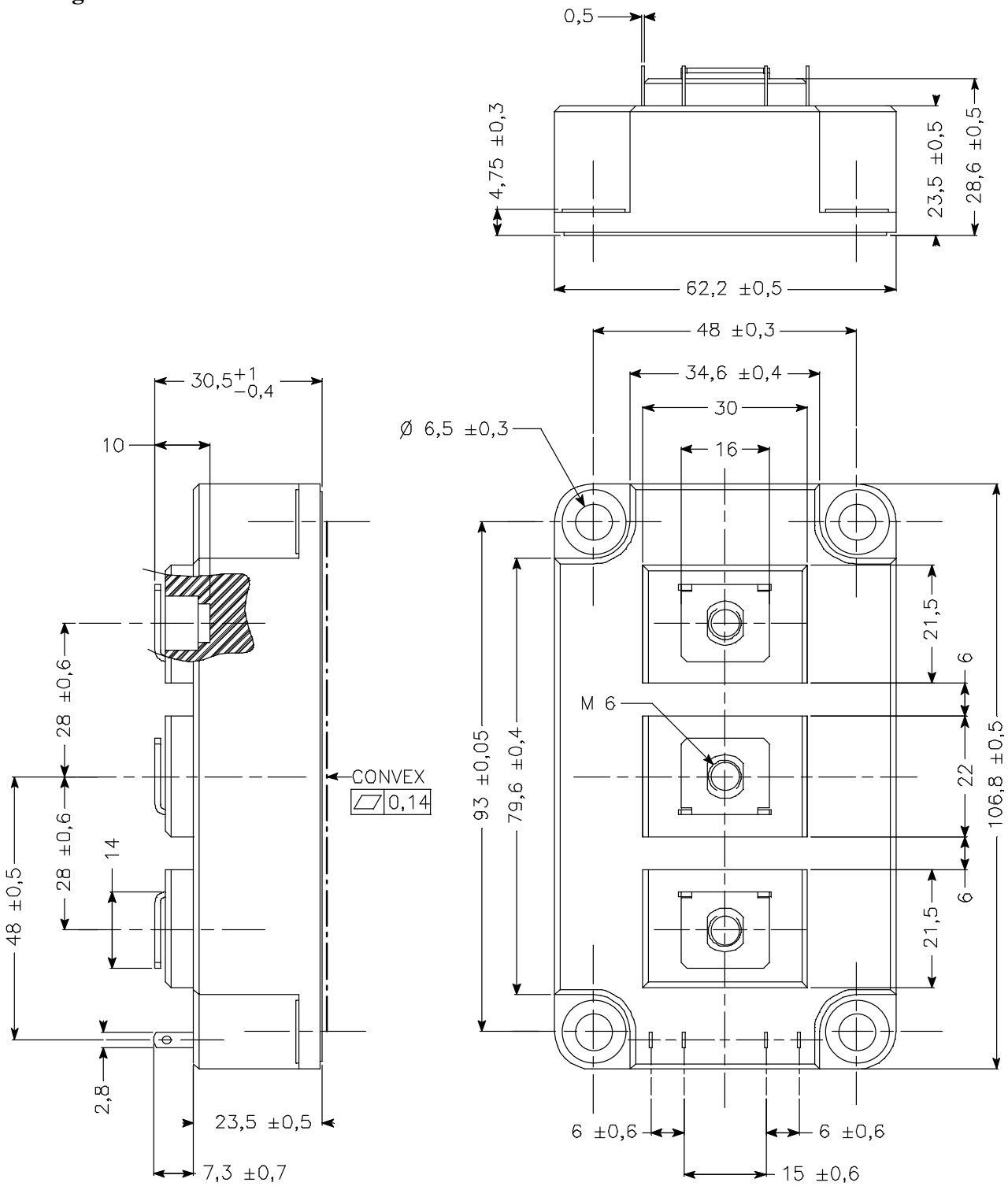
Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_F	Diode Forward Voltage	I_F = 200A V_{GE} = 0V	T_j = 25°C		1.6	2.1	V
			T_j = 125°C		1.6		
E_{rec}	Reverse Recovery Energy	I_F = 200A V_R = 600V di/dt =900A/µs	T_j = 125°C		17		mJ
Q_{rr}	Reverse Recovery Charge	I_F = 200A V_R = 600V di/dt =900A/µs	T_j = 25°C		20		µC
			T_j = 125°C		36		

Thermal and package characteristics

Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case		IGBT			0.12	°C/W
			Diode			0.20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	
Wt	Package Weight					380	g

Package outline



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.